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## FCA20N60F

May 2014

# N-Channel SuperFET® FRFET® MOSFET 600 V, 20 A, 190 m $\Omega$

## **Features**

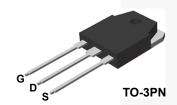
- 650 V @ T<sub>J</sub> = 150°C
- Typ.  $R_{DS(on)}$  = 150 m $\Omega$
- Fast Recovery Type (Typ. T<sub>rr</sub> = 160 ns )
- Ultra Low Gate Charge (Typ.  $Q_g = 75 \text{ nC}$ )
- Low Effective Output Capacitance (Typ. C<sub>oss(eff.)</sub> = 165 pF )
- 100% Avalanche Tested
- · RoHS Compliant

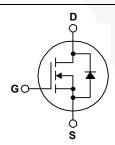
## **Applications**

- · LCD / LED / PDP TV
- Solar Inverter
- AC-DC Power Supply

## **Description**

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SuperFET FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FCA20N60F	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		600	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)		20 12.5	A A	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	60	Α	
V <sub>GSS</sub>	Gate-Source voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		690	mJ	
I <sub>AR</sub>	Avalanche Current (Note 1)		20	Α	
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		20.8	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	50	V/ns	
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate . bove 25°C		208 1.67	W W/°C	
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

#### **Thermal Characteristics**

Symbol	Parameter	FCA20N60F	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.6	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCA20N60F	FCA20N60F	TO-3PN	Tube	N/A	N/A	30 units

## **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics			I	1	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_J = 25^{\circ}\text{C}$	600			V
		$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_J = 150^{\circ}\text{C}$		650		V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.6		V/°C
BV <sub>DSS</sub>	Drain-Source Avalanche Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 20 A		700		V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 480 V, T <sub>C</sub> = 125°C			10 100	μ <b>Α</b> μ <b>Α</b>
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0V			-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	1	0.15	0.19	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 10 A	\	17		S
Dynamic C	Characteristics					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		2370	3080	pF
C <sub>oss</sub>	Output Capacitance		-	1280	1665	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			95		pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		65	85	pF
Coss eff.	Effective Output Capacitance	$V_{DS}$ = 0 V to 400 V, $V_{GS}$ = 0 V		165		pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 300 \text{ V}, I_D = 20 \text{ A},$	/	62	135	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25\Omega$	/	140	290	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			230	470	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	^	65	140	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 480 V, I <sub>D</sub> = 20 A,		75	98	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		13.5	18	nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		36		nC
Drain-Sour	rce Diode Characteristics and Maximur	n Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Dio	de Forward Current			20	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	orward Current			60	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 20 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 20 A,		160		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> /dt = 100 A/μs		1.1		μС

#### Notes:

<sup>1.</sup> Repetitive rating: pulse-width limited by maximum junction temperature.

<sup>2.</sup> I $_{AS}$  = 10 A, V $_{DD}$  = 50 V, R $_{G}$  = 25  $\Omega$ , starting T $_{J}$  = 25°C.

 $<sup>3.</sup>I_{SD} \leq 20~A,~di/dt \leq 1200~A/\mu s,~V_{DD} \leq BV_{DSS},~starting~T_J = 25^{\circ}C.$ 

<sup>4.</sup> Essentially independent of operating temperature typical characteristics.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

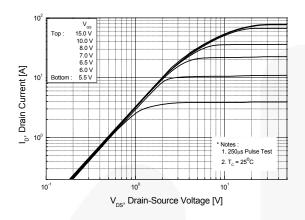


Figure 2. Transfer Characteristics

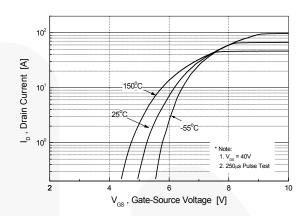


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

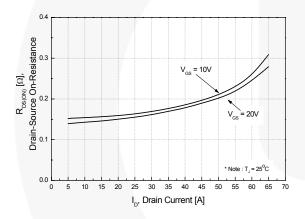
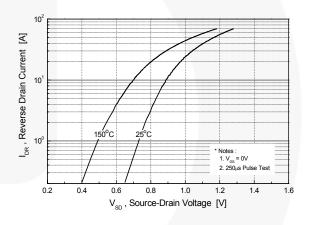


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



**Figure 5. Capacitance Characteristics** 

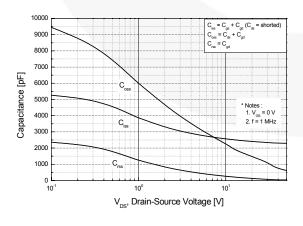
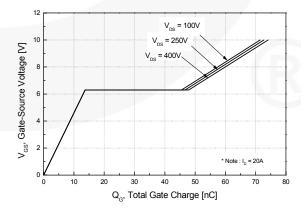


Figure 6. Gate Charge Characteristics



## Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

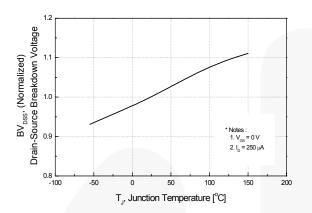


Figure 8. On-Resistance Variation vs. Temperature

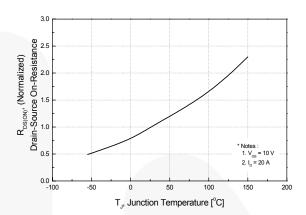


Figure 9-1. Maximum Safe Operating Area

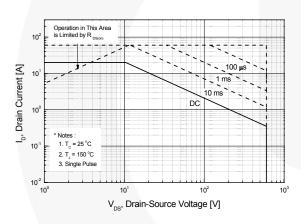


Figure 10. Maximum Drain Current vs. Case Temperature

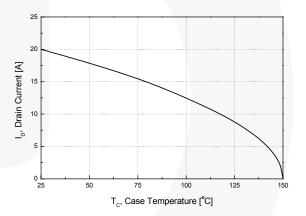
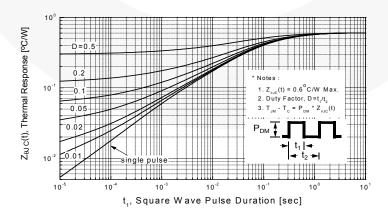


Figure 11. Transient Thermal Response Curve



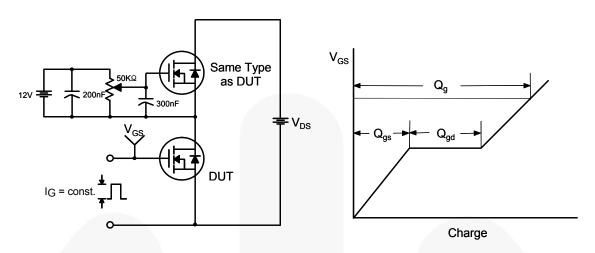


Figure 12. Gate Charge Test Circuit & Waveform

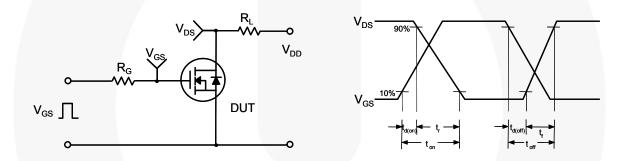


Figure 13. Resistive Switching Test Circuit & Waveforms

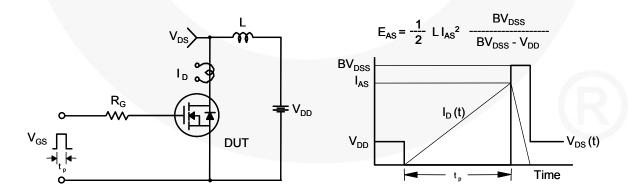


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

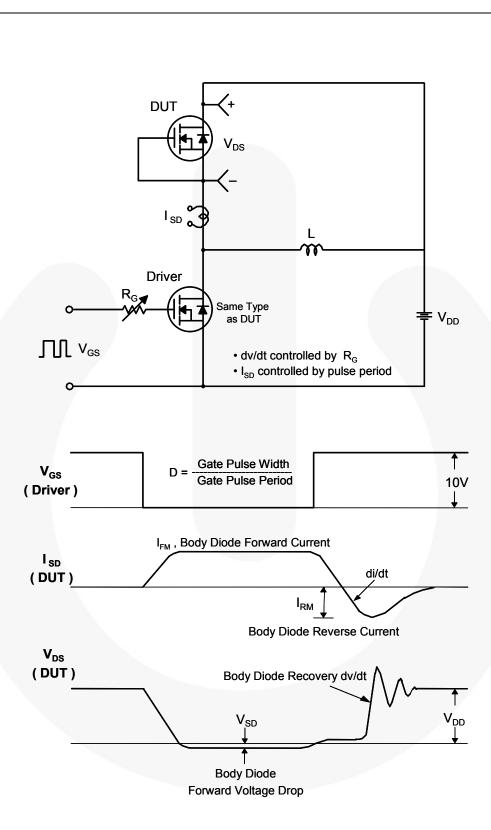
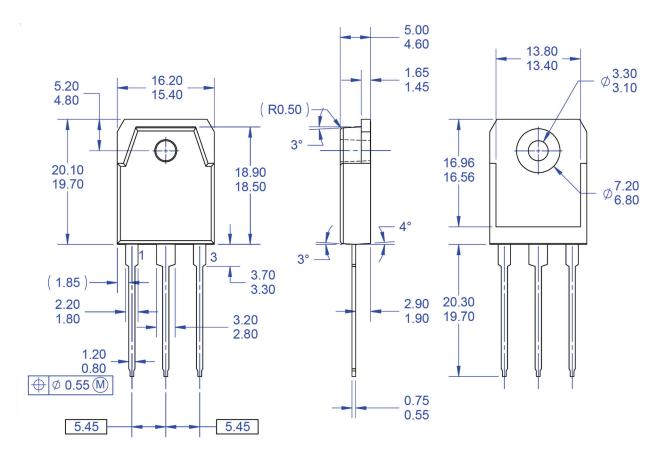
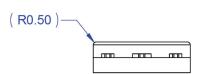


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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- NOTES: UNLESS OTHERWISE SPECIFIED
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   B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSION AND TOLERANCING PER
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## Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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